



DESCRIPTION

The 3400 uses advanced trench technology to provide excellent RDS(ON) and low gate charge. This device is suitable for use as a load switch or in PWM applications.

Product Summary

RDS(ON) <30m Ω @ VGS=10V

RDS(ON) <40mΩ @ VGS=4.5V

GENERAL FEATURES

- Trench Power LV MOSFET technology
- High density cell design for low RDS(ON)
- High Speed switching

Application

- Battery protection
- Load switch
- Power management

■ Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V _{DS}	30	V
Gate-source Voltage		V _{GS}	±20	V
Drain Current	T _C =25°C	I _D	5.6	A
	T _C =75°C		4.5	
Pulsed Drain Current ^A		I _{DM}	30	A
Total Power Dissipation	T _C =25°C	P _D	1.2	W
	T _C =70°C		0.9	W
Thermal Resistance Junction-to-Ambient @ Steady State B		R _{θJC}	105	°C/W
Junction and Storage Temperature Range		T _J , T _{STG}	-55~+150	°C

